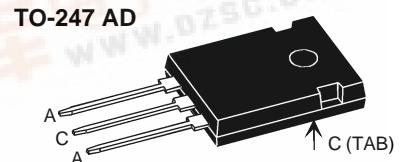
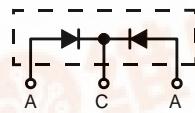




## Power Schottky Rectifier with common cathode

$I_{FAV} = 2 \times 25 \text{ A}$   
 $V_{RRM} = 100 \text{ V}$   
 $V_F = 0.65 \text{ V}$

$V_{RSM}$	$V_{RRM}$	Type
V	V	
100	100	DSSK 50-01A



A = Anode, C = Cathode , TAB = Cathode

Symbol	Conditions	Maximum Ratings	
$I_{FRMS}$		70	A
$I_{FAV}$	$T_c = 155^\circ\text{C}$ ; rectangular, $d = 0.5$	25	A
$I_{FAV}$	$T_c = 155^\circ\text{C}$ ; rectangular, $d = 0.5$ ; per device	50	A
$I_{FSM}$	$T_{VJ} = 45^\circ\text{C}$ ; $t_p = 10 \text{ ms}$ (50 Hz), sine	450	A
$E_{AS}$	$I_{AS} = 11 \text{ A}$ ; $L = 180 \mu\text{H}$ ; $T_{VJ} = 25^\circ\text{C}$ ; non repetitive	13	mJ
$I_{AR}$	$V_A = 1.5 \cdot V_{RRM}$ typ.; $f=10 \text{ kHz}$ ; repetitive	1.1	A
( $dv/dt$ ) <sub>cr</sub>		5000	V/ $\mu$ s
$T_{VJ}$		-55...+175	°C
$T_{VJM}$		175	°C
$T_{stg}$		-55...+150	°C
$P_{tot}$	$T_c = 25^\circ\text{C}$	135	W
$M_d$	mounting torque	0.8...1.2	Nm
Weight	typical	6	g

Symbol	Conditions	Characteristic Values	
		typ.	max.
$I_R$	① $T_{VJ} = 25^\circ\text{C}$ $V_R = V_{RRM}$ $T_{VJ} = 125^\circ\text{C}$ $V_R = V_{RRM}$	1 10	mA mA
$V_F$	$I_F = 25 \text{ A}; T_{VJ} = 125^\circ\text{C}$ $I_F = 25 \text{ A}; T_{VJ} = 25^\circ\text{C}$ $I_F = 50 \text{ A}; T_{VJ} = 125^\circ\text{C}$	0.65 0.80 0.77	V V V
$R_{thJC}$		0.25	1.1 K/W
$R_{thCH}$			K/W

### Features

- International standard package
- Very low  $V_F$
- Extremely low switching losses
- Low  $I_{RM}$ -values
- Epoxy meets UL 94V-0

### Applications

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

### Advantages

- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching
- Low losses

Dimensions see outlines.pdf

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %  
Data according to IEC 60747 and per diode unless otherwise specified

IXYS reserves the right to change limits, Conditions and dimensions.

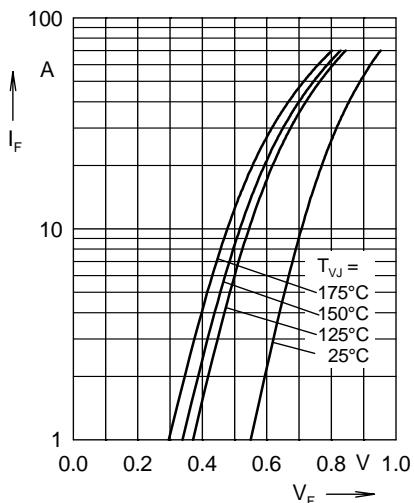


Fig. 1 Maximum forward voltage drop characteristics

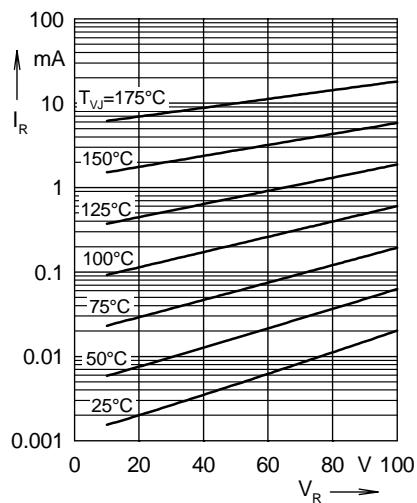


Fig. 2 Typ. value of reverse current  $I_R$  versus reverse voltage  $V_R$

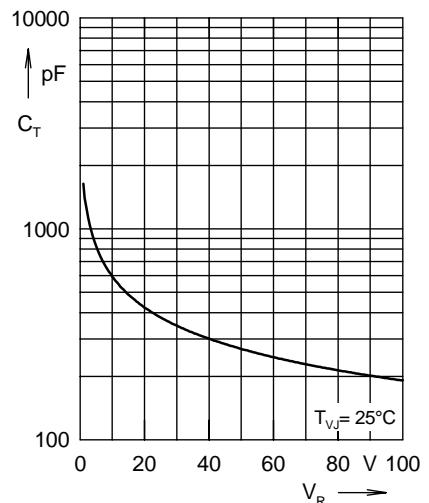


Fig. 3 Typ. junction capacitance  $C_T$  versus reverse voltage  $V_R$

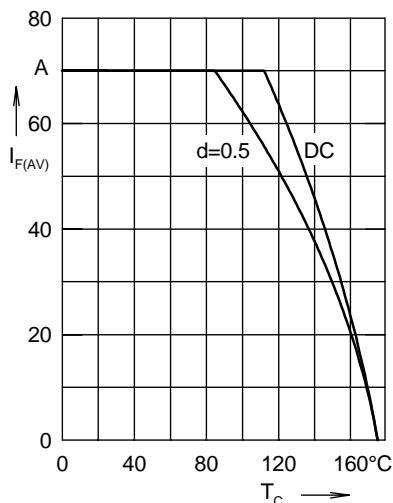


Fig. 4 Average forward current  $I_{F(AV)}$  versus case temperature  $T_c$

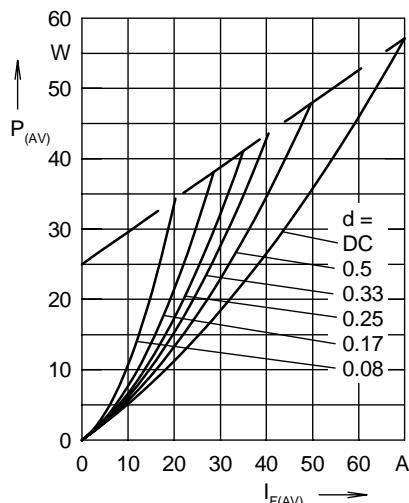


Fig. 5 Forward power loss characteristics

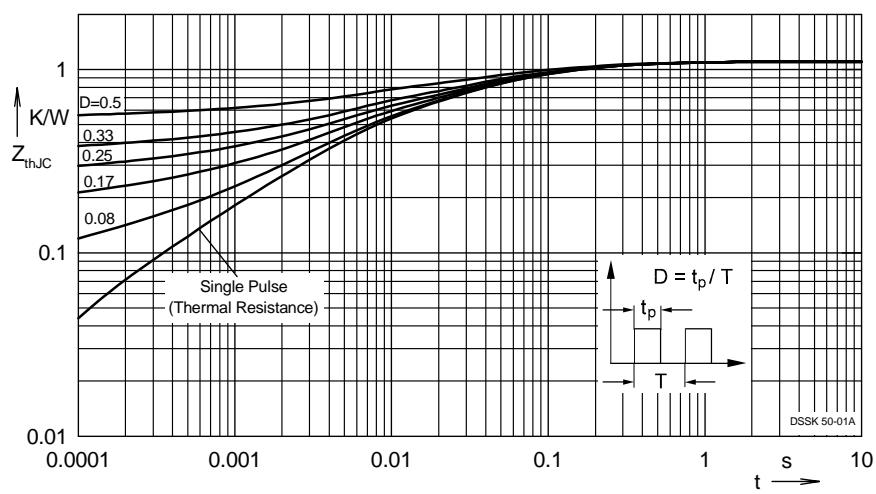


Fig. 6 Transient thermal impedance junction to case at various duty cycles

Note: All curves are per diode